

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,953,720 B2  
DATED : October 11, 2005  
INVENTOR(S) : John T. Moore et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, add the following:

-- 6,707,712 3/2004 Lowery --.

OTHER PUBLICATIONS, add the following:

-- Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, *J. Am. Ceram. Soc.* 82 (1999) 2934-2936.

Thornburg, D.D., Memory switching in amorphous arsenic triselenide, *J. Non-Cryst. Solids* 11 (1972) 113-120. --.

“Bernede, J.C. Polarized memory switching in MIS thin films, *Thin Solid Films* 87 (1981) 155-160.” should read

-- Bernede, J.C. Polarized memory switching in MIS thin films, *Thin Solid Films* 81 (1981) 155-160. --;

“Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, *J. Non-Cryst. Solids* 222 (1997) 134-143.” should read

-- Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, *J. Non-Cryst. Solids* 222 (1997) 137-143. --;

“Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=NI, BI), *Mat. Chem. And Physics* 28 (1991) 253-258.” should read

-- Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), *Mat. Chem. And Physics* 28 (1991) 253-258. --;

“Snell, A.J.; Hajto, J.; Rosa, M.J.; Osborne, L.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a -Si:H/metal thin films structures, *Mat. Res. Soc. Symp. Proc.* V 297, 1993, 1017-1021.” should read

-- Snell, A.J.; Hajto, J.; Rose, M.J.; Osborne, L.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a -Si:H/metal thin films structures, *Mat. Res. Soc. Symp. Proc.* V 297, 1993, 1017-1021. --; and

“Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -SI:H memory devices, *Mat. Res. Soc. Symp. Proc.* V 258, 1992, 1075-1080” should read

-- Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, *Mat. Res. Soc. Symp. Proc.* V 258, 1992, 1075-1080. --.

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 3.

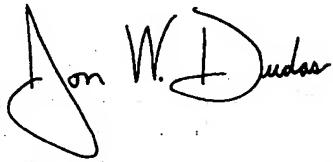
Line 56, "to second" should read -- to a second --; and

Column 7.

Line 63, "carried Out" should read -- carried out --.

Signed and Sealed this

Twenty-eighth Day of March, 2006



JON W. DUDAS  
Director of the United States Patent and Trademark Office